

## NCE P-Channel Enhancement Mode Power MOSFET

### Description

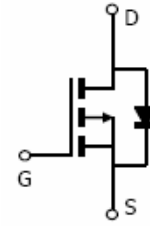
The NCE40P13S uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

### General Features

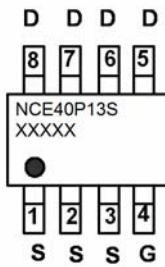
- $V_{DS} = -40V, I_D = -13A$   
 $R_{DS(ON)} < 15m\Omega @ V_{GS} = -10V$   
 $R_{DS(ON)} < 18m\Omega @ V_{GS} = -4.5V$
- High density cell design for ultra low  $R_{dson}$
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

### Application

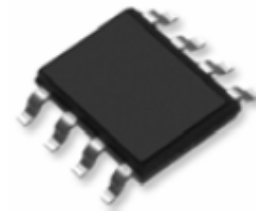
- Power switching application
- Hard switched and high frequency circuits
- DC-DC converter



Schematic diagram



Marking and pin assignment



SOP-8 top view

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE40P13S	NCE40P13S	SOP-8	Ø330mm	12mm	4000 units

### Absolute Maximum Ratings ( $T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	-40	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	-13	A
Drain Current-Continuous( $T_C = 100^\circ C$ )	$I_D(100^\circ C)$	-9	A
Pulsed Drain Current	$I_{DM}$	50	A
Maximum Power Dissipation	$P_D$	2.5	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ C$

### Thermal Characteristic

Thermal Resistance ,Junction-to-Ambient(Note 2)	$R_{\theta JA}$	50	$^\circ C/W$
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## Electrical Characteristics ( $T_A=25^{\circ}\text{C}$ unless otherwise noted)

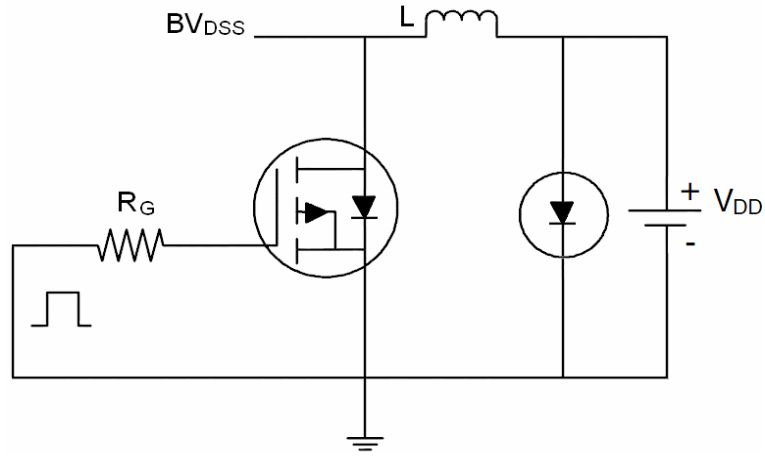
Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-40	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-40V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics (Note 3)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.3	-2	-2.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-12A$	-	12	15	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=-15V, I_D=-10A$	35	-	-	S
<b>Dynamic Characteristics (Note 4)</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=-20V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	2800	-	PF
Output Capacitance	$C_{oss}$		-	320	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	220	-	PF
<b>Switching Characteristics (Note 4)</b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-20V, R_L=2\Omega$ $V_{GS}=-10V, R_{GEN}=6\Omega$	-	11	-	nS
Turn-on Rise Time	$t_r$		-	75	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	89	-	nS
Turn-Off Fall Time	$t_f$		-	35	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=-20V, I_D=-12A,$ $V_{GS}=-10V$	-	40	-	nC
Gate-Source Charge	$Q_{gs}$		-	6	-	nC
Gate-Drain Charge	$Q_{gd}$		-	12	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=-12A$	-	-	1.2	V
Diode Forward Current (Note 2)	$I_S$		-	-	-13	A

### Notes:

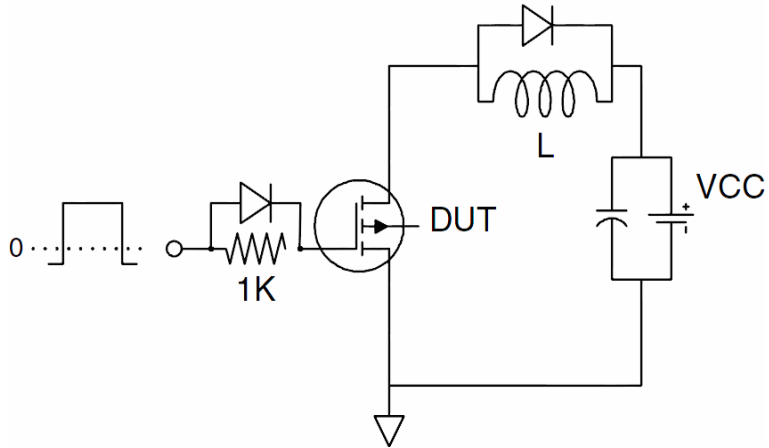
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production

## Test Circuit

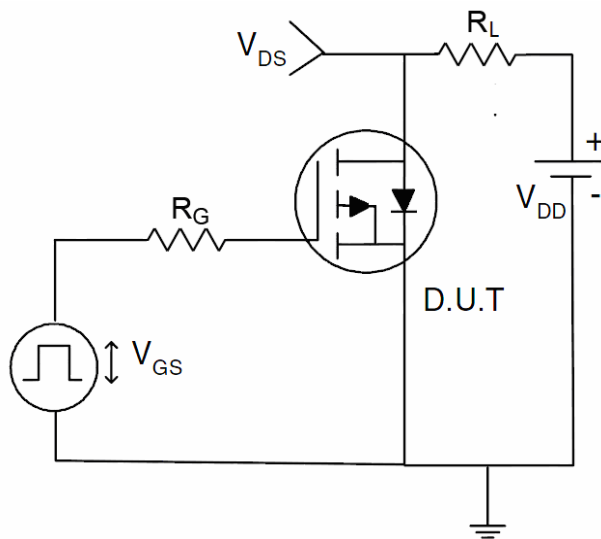
### 1) E<sub>AS</sub> Test Circuit



### 2) Gate Charge Test Circuit



### 3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

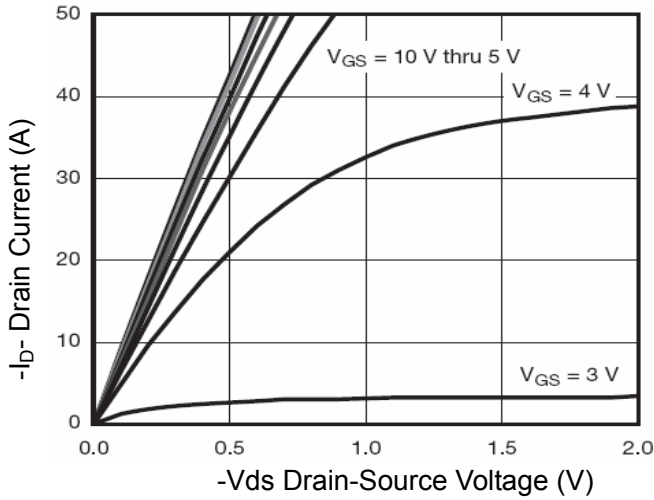


Figure 1 Output Characteristics

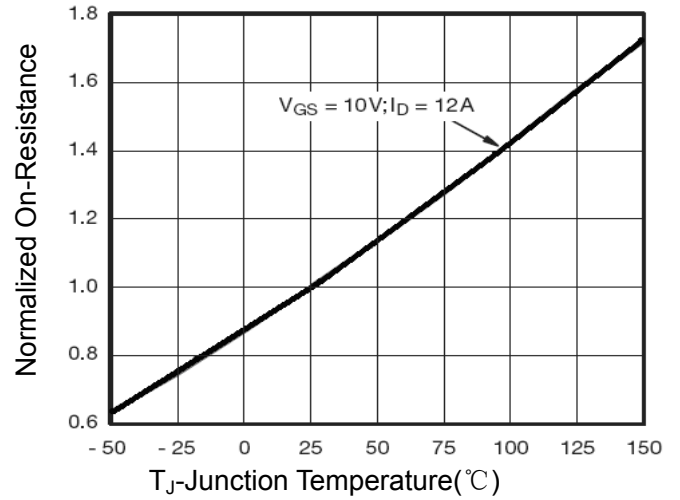


Figure 4 Rdson-Junction Temperature

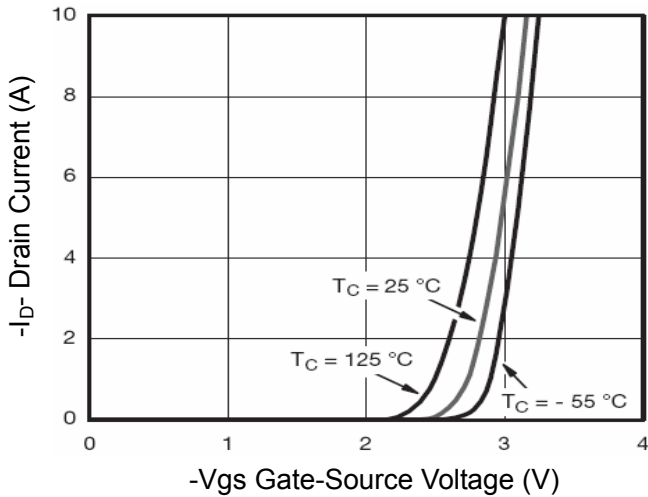


Figure 2 Transfer Characteristics

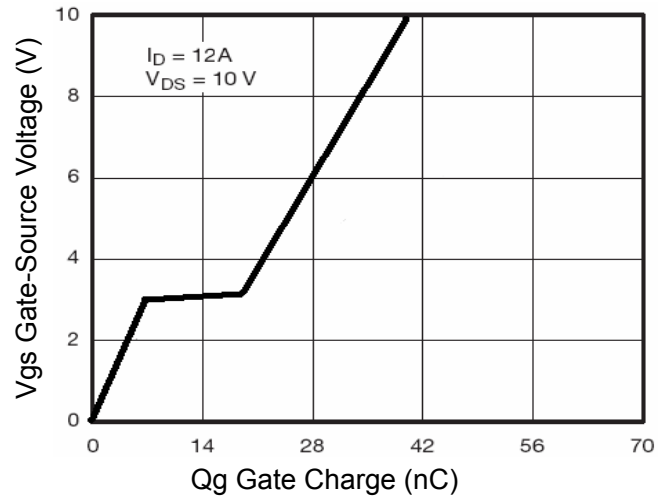


Figure 5 Gate Charge

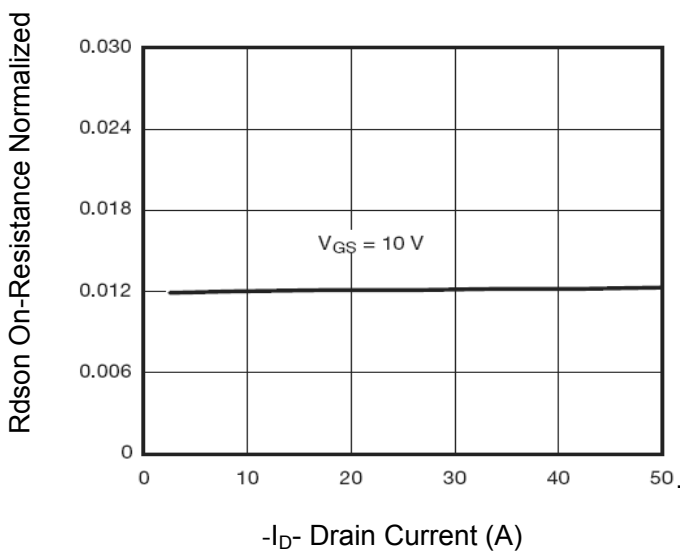


Figure 3 Rdson- Drain Current

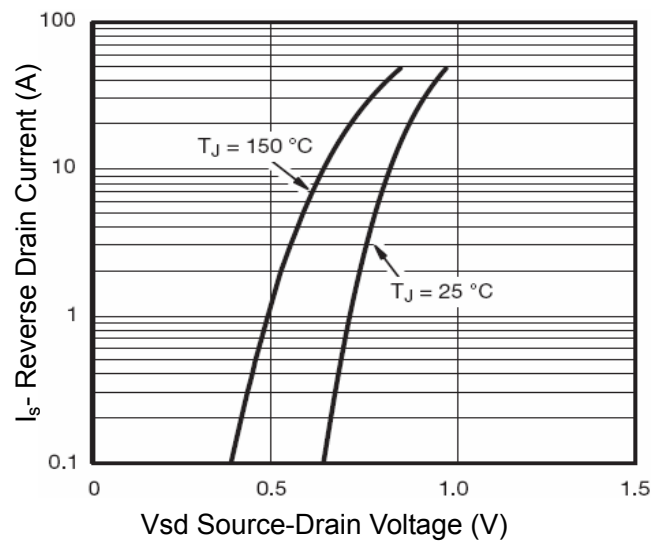
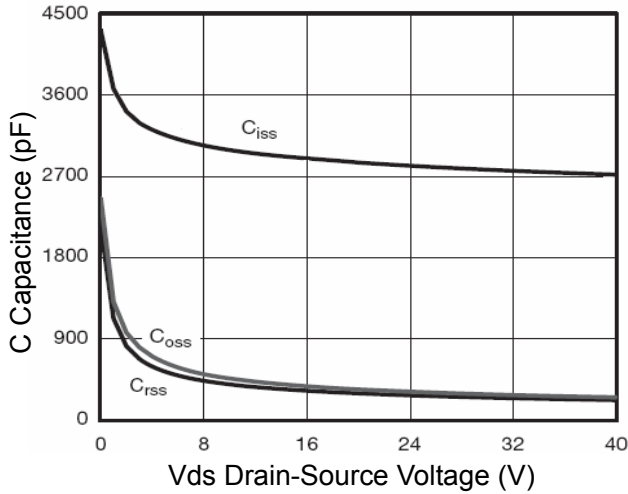
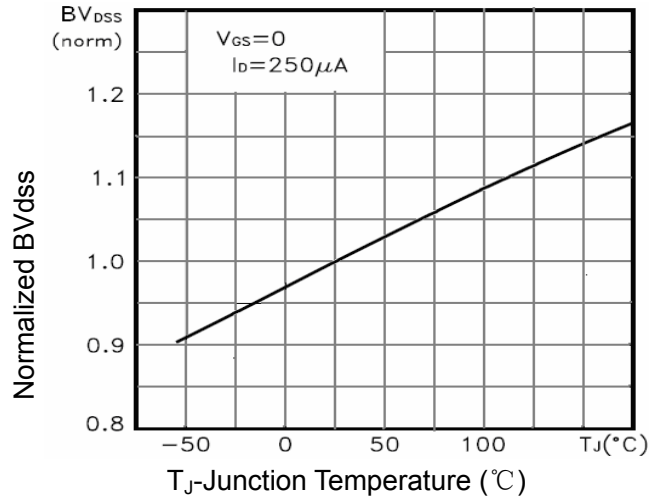


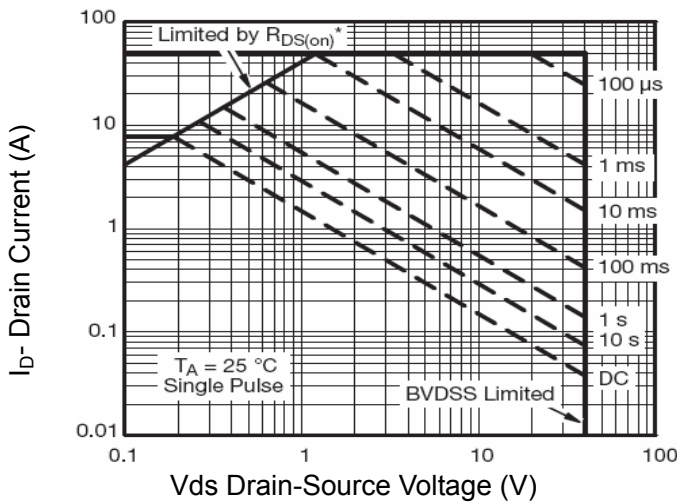
Figure 6 Source- Drain Diode Forward



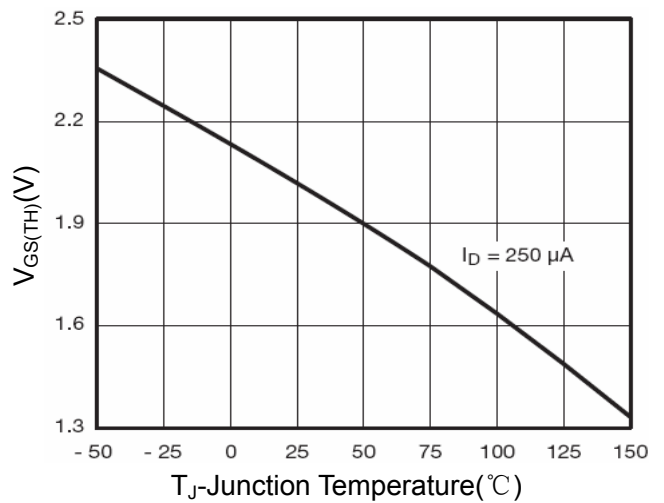
**Figure 7 Capacitance vs Vds**



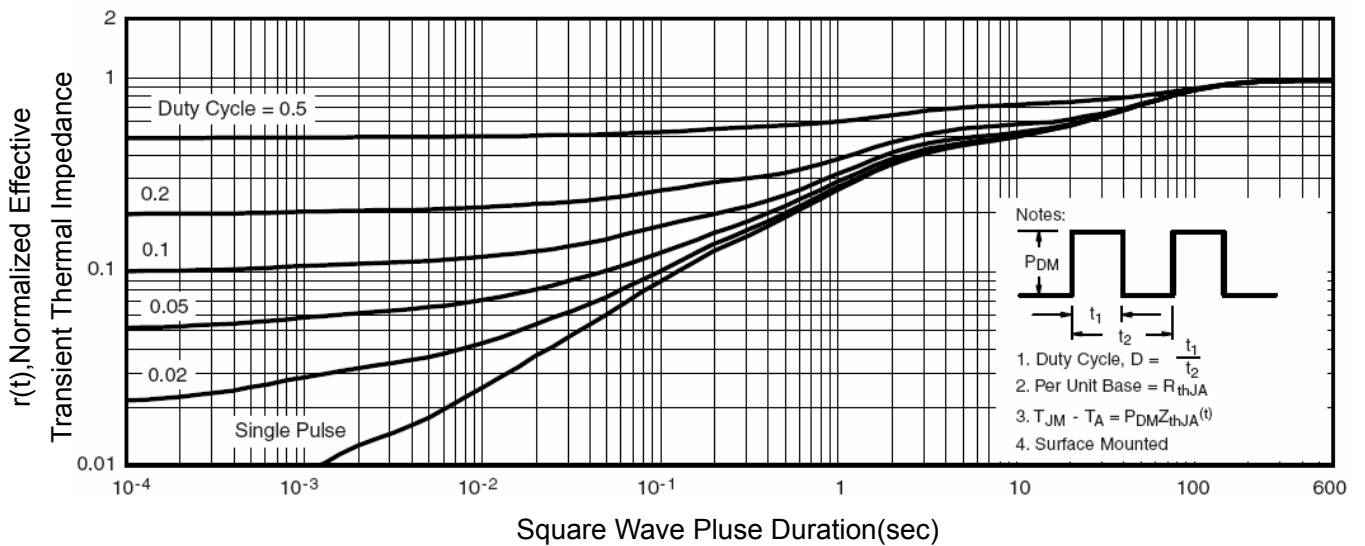
**Figure 9  $BV_{DSS}$  vs Junction Temperature**



**Figure 8 Safe Operation Area**

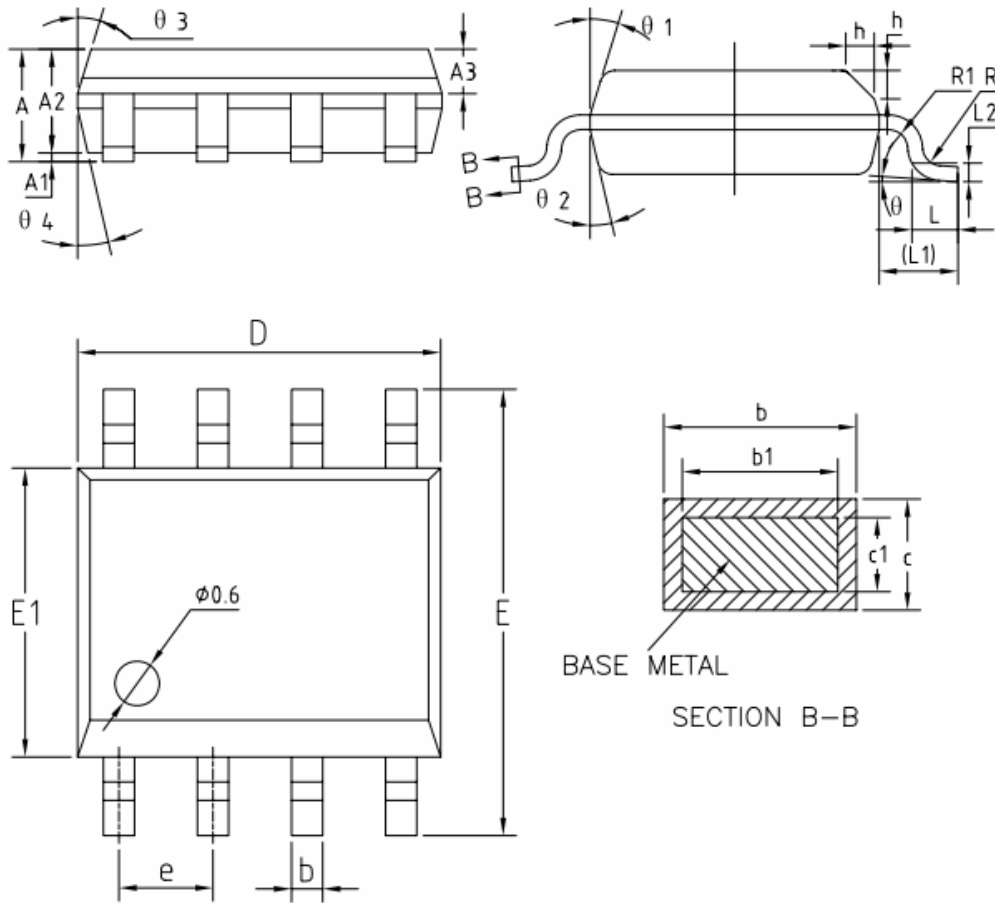


**Figure 10  $V_{GS(th)}$  vs Junction Temperature**



**Figure 11 Normalized Maximum Transient Thermal Impedance**

## SOP-8 Package Information



COMMON DIMENSIONS  
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	1.35	1.55	1.75
A1	0.10	0.15	0.25
A2	1.25	1.40	1.65
A3	0.50	0.60	0.70
b	0.38	-	0.51
b1	0.37	0.42	0.47
c	0.18	-	0.25
c1	0.17	0.20	0.23
D	4.80	4.90	5.00
E	5.80	6.00	6.20
E1	3.80	3.90	4.00
e	1.17	1.27	1.37
L	0.45	0.60	0.80
L1	1.04REF		
L2	0.25BSC		
R	0.07	-	-
R1	0.07	-	-
h	0.30	0.40	0.50
$\theta$	0°	-	8°
$\theta_1$	15°	17°	19°
$\theta_2$	11°	13°	15°
$\theta_3$	15°	17°	19°
$\theta_4$	11°	13°	15°

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